

REPLACEMENT SHEET

Title: FABRICATION METHOD FOR A
SEMICONDUCTOR STRUCTURE
HAVING A PARTLY FILLED TRENCH
Applicant: Hansel et al.
Serial No. 10/660,091 Ref No.: 1406/166

FIG 1A

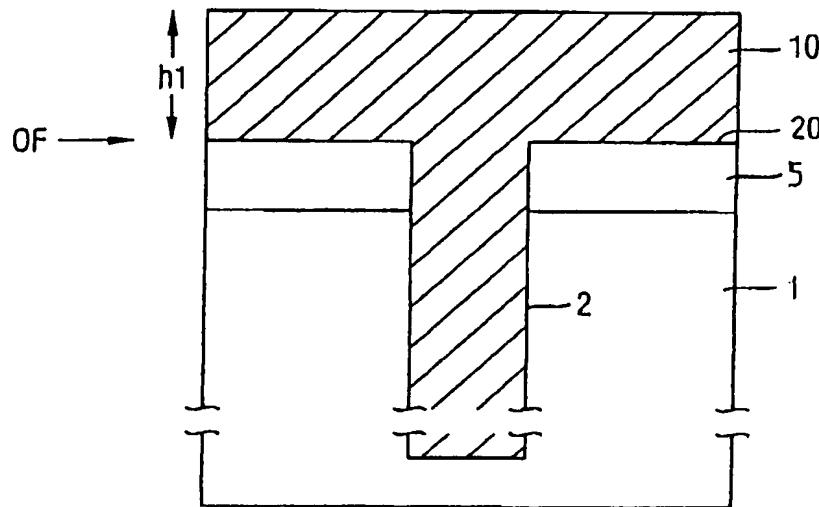
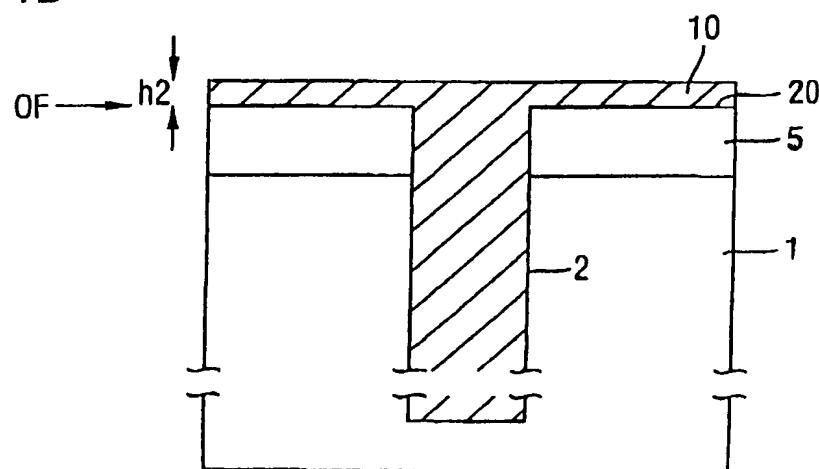


FIG 1B



REPLACEMENT SHEET
Title: FABRICATION METHOD FOR A
SEMICONDUCTOR STRUCTURE
HAVING A PARTLY FILLED TRENCH
Applicant: Hansel et al.
Serial No. 10/660,091 Ref No.: 1406/166

FIG 1C

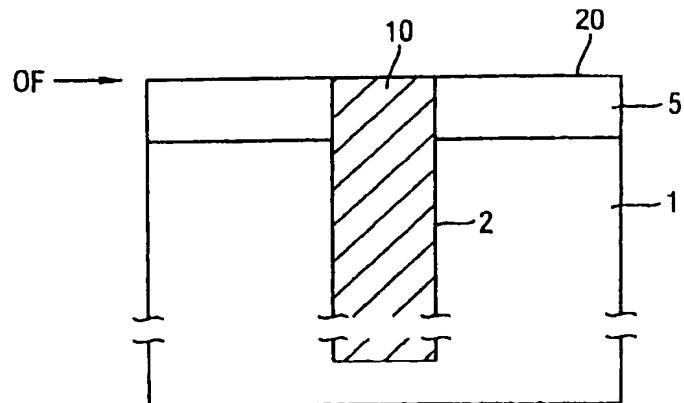
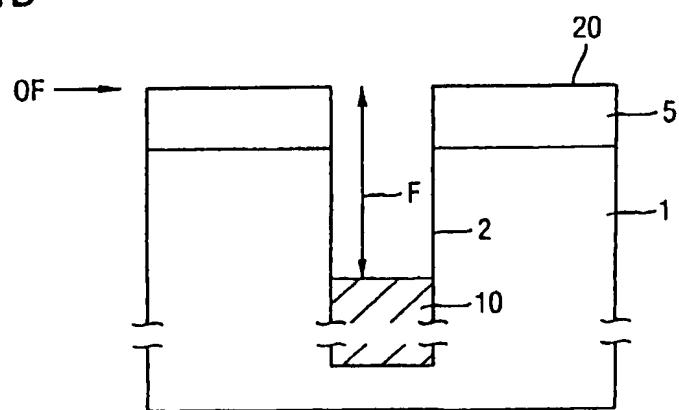
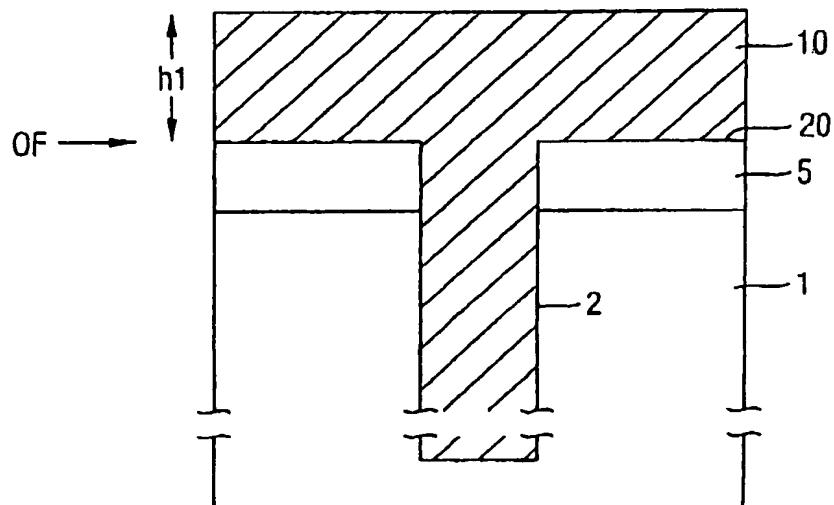


FIG 1D



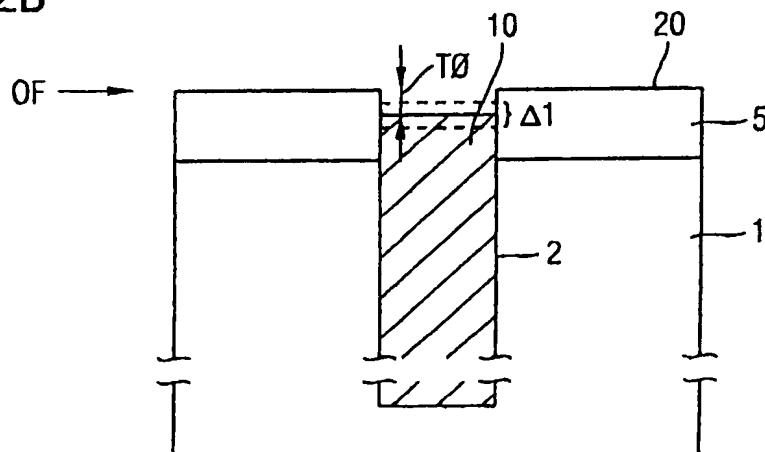
REPLACEMENT SHEET
Title: FABRICATION METHOD FOR A
SEMICONDUCTOR STRUCTURE
HAVING A PARTLY FILLED TRENCH
Applicant: Hansel et al.
Serial No. 10/660,091 Ref No.: 1406/166

FIG 2A



(PRIOR ART)

FIG 2B

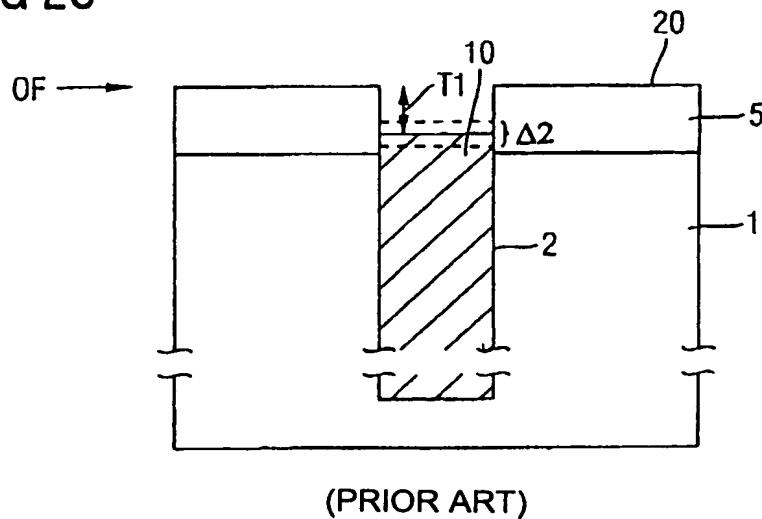


(PRIOR ART)

REPLACEMENT SHEET

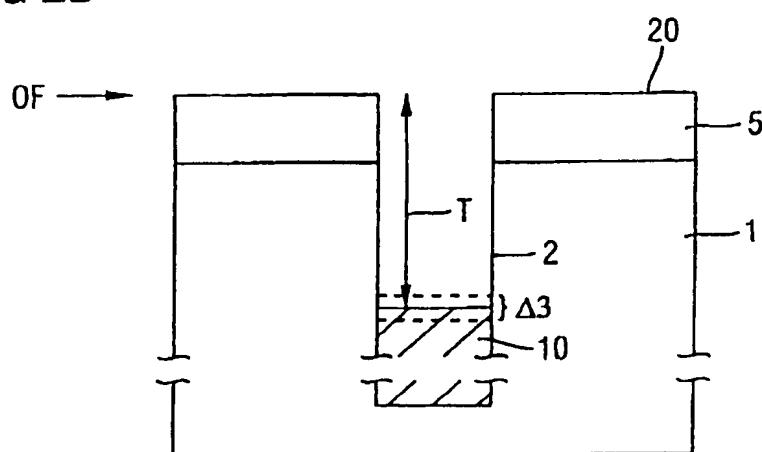
Title: FABRICATION METHOD FOR A
SEMICONDUCTOR STRUCTURE
HAVING A PARTLY FILLED TRENCH
Applicant: Hansel et al.
Serial No. 10/660,091 Ref No.: 1406/166

FIG 2C



(PRIOR ART)

FIG 2D



(PRIOR ART)